

Investigation of microstructure of irradiated multilayer ZrN/Si₃N₄ thin coatings revealed by X-ray diffraction techniques

Alex Ulyanenkov¹, <u>Svetlana Vlasenko²</u>, Alexander Mikhalychev², Vladimir Uglov³, Grégory Abadias⁴, Jacques O'Connell⁵, Arno Janse van Vuuren⁵

¹Atomicus GmbH, Karlsruhe, Germany, ²Atomicus OOO, Minsk, Belarus, ³Department of Theoretical Physics, Belarusian State University, Minsk, Belarus, ⁴Institut Pprime, CNRS, Université de Poitiers, Poitiers, France, ⁵Centre for High Resolution Transmission Electron Microscopy, Nelson Mandela Metropolitan University, Port Elizabeth, South Africa



Why nitride-based thin films?

Various applications as protective coatings

- o microelectronics,
- \circ optics,
- nuclear applications,
- o ...

Properties suitable for nuclear applications:

- high melting point
- high hardness
- stability under elevated temperatures
- wear and corrosion resistance
- good thermal conductivity
- good mechanical properties

Why multilayers?

- Enhancement of the properties: the presence of interfaces and boundaries in the materials acts as an effective sink for the radiation induced point defects.
- Easy to control experimental growth and thickness of the sample.

Radiation tolerant

coating materials

estimation of the effects

of radiation damage

modification of microstructure

under the irradiation process.



Motivation of the research

[001]

Techniques to characterize thin films:

- Reciprocal space mapping (RSM),
- Pole figures
- Grazing incidence XRD (GIXRD)
- θ/2θ scanning (coplanar geometry)
- Non-coplanar geometry



- access to a larger number of Bragg reflections
- no tilt of the sample (important for high-temperature measurements)
- no rotation of the sample
- insufficient resolution: a set of two orthogonal Soller slits are used
- coplanar GIXRD does not permit to cover the whole range of ψ angles (because of 2 θ limits)





Purposes of the research:

- evaluate microstructural parameters using theoretical analysis of XRD data, measured in non-coplanar geometry
- estimate if the microstructure undergoes changes under irradiation
- compare the results of XRD and HRTEM

Investigation techniques:

- □ X-ray diffraction (XRD)
- High-resolution transmission electron microscopy (HRTEM)
- Theoretical analysis



Experimental: general

Diffractometer setup:

- Cu K α radiation (λ = 0.154056 nm) \bigcirc
- parallel beam geometry 0
- set of two orthogonal receiving Soller slits 0

Soller slits Detector θ sample stage X-ray source

+

irr.

Non-coplanar measurement configuration

Samples:

- crystalline/amorphous multilayers ZrN/Si₃N₄
- single crystal Si (001) substrate 0
- total thickness of each multilayer: Ο 300 nm

Irradiation conditions:

- 30 keV He+ ions Ο
- integral dose: $5 \cdot 10^{16} cm^{-2}$ Ο

- **ML-1**: 5 nm/5 nm
 - **ML-2**: 10 nm/5 nm
- **ML-3**: 5 nm/2 nm
- **ML-4**: 10 nm/0.4 nm unirr.



ATOMICUS Experimental: workflow of the XRD measurement process



ATOMICUS Experimental: pole figures



to the sample surface

ATOMICUS Experimental: best conditions for measuring scans



ATOMICUS Experimental: XRD measurements



XRD profiles: polycrystalline ZrN layers



Instrumental function: LaB6 powder





Theoretical analysis



Grain sizes distribution: Gauss distribution function

$$f(x) = \frac{1}{\sqrt{2^{\pi \sigma}}} \exp \left[-\frac{(x - m_{hkl})^2}{2^{\sigma 2}} \right]$$





When applying an ellipsoidal grain shape model, the size distribution function becomes anisotropic, with the appearing dependence of the reflection intensity on the *hkl*.

$$m_{hkl} = \frac{m}{\sqrt{1 + \left(\frac{1}{e^2} - 1\right)\cos^2\psi}},$$
$$\cos\psi = \frac{l}{\sqrt{h^2 + k^2 + l^2}}, \qquad e = \frac{c}{a}$$



Assuming ellipsoidal grains, the *hkl*-dependent size broadening is given by

$$\begin{aligned} A_{size}^{hkl}(L) &= \frac{1}{6} \left(2m^3 + 6m\sigma^2 - 3\sigma^2 |L| \right) + \frac{1}{6} \exp\left[-\frac{(m-|L|)^2}{2\sigma^2} \right] \sqrt{\frac{2}{\pi}} \sigma \left(-2m^2 - 4\sigma^2 + |L|(m+|L|) \right) - \\ &- \frac{1}{6} \left\{ 2m^3 + 6m\sigma^2 - 3\sigma^2 |L| - 3m^2 |L| + |L|^3 \right\} \operatorname{Erfc}\left[\frac{|L| - m}{\sqrt{2}\sigma} \right] \end{aligned}$$

For accounting the **instrumental effects**, a set of LaB6 profiles were measured and used as instrumental profiles I_{instr}^{hkl}



The instrumental function plays a crucial role in the non-coplanar measurements.





The reflections, obtained under different ψ angles, are combined into a single scan for the simultaneous fitting with a theoretically simulated curve.

Four unirradiated and **three irradiated by the He+** ions samples were evaluated to estimate the modification of sample microstructure under the irradiation process.





The measured **direction-dependent broadening** was in agreement with the assumed shape.



The microstructural parameters obtained from the fitting of the whole scan and those obtained solely for 020 reflection ($\psi \approx 90$) are in a very good agreement, which confirms the correctness of the size estimation in the direction parallel to the sample surface.

For the sample ML-4, the multiple reflections 002 and 004, 111 and 222 are observed, and *mhkl* for these reflections are close each to other, which confirms the absence of the line broadening caused by the defects.



Experimental: TEM measurements

Preparation of the experiment:

- specimens were prepared using
 FEI Helios Nanolab 650 focused ion beam
- initial milling 30 keV Ga ions
- final thinning 5 keV
- polishing 2keV and 500 eV
- analysis JEOL JEM 2100 LaB6 transmission electron microscope (200 kV)



Image of grains



High-resolution TEM





Unirradiated ML-3



Irradiated by He+ ML-3



ellipsoidal grain

After the irradiation:

- the thickness of the ZrN is almost the same,
- the thickness of the amorphous layers undergoes a significant increase.

Possible explanation:

bubble formation during the irradiation

deformation of the crystalline/amorphous interfaces due to the appearance of residual stresses

5 nm

SIN

ZrN



Microstructural parameters: XRD vs HRTEM



A good consistence between the XRD and HRTEM results for unirradiated samples confirms the validity of the used theoretical model.

A good agreement between the results of XRD and HRTEM for irradiated samples means that after irradiation no significant amount of defects appeared.

Grains size in the samples after irradiation does not differ significantly from that before the irradiation.



The microstructural parameters of ZrN/Si3N4 multilayer thin coatings have been evaluated using X-ray diffraction technique in non-coplanar geometry.

The non-coplanar X-ray diffraction geometry gives an access to a larger number of Bragg reflections comparing to the case of a coplanar configuration.

The technique enables to perform a comprehensive and reliable analysis of the samples possessing the anisotropy of physical properties.

Using the theoretical model for ellipsoidal grains, the sizes of grains in parallel and normal to the sample surface directions were calculated.

The results obtained from XRD measurements are in a good agreement with those evaluated from HRTEM and STEM.

Comparing the results of XRD analysis and HRTEM for unirradiated and irradiated samples, the microstructure of investigated samples is proved to do not undergo a significant change under the irradiation process.

The proposed approach can also be extended to include other sources of diffraction line broadening which occurs in different materials.



Thank you for your attention!

svetlana.vlasenko@atomicus.by